



Product/Process Change Notice - PCN 14_0067 Rev. A

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This notice is to inform you of a change that will be made to certain ADI products (see Material Report). Any issues with this PCN or requirements to qualify the change (additional data or samples) must be sent to ADI within 30 days of publication date. ADI contact information is listed below.

Note: Revised fields are indicated by a red field name. See Appendix B for revision history.

PCN Title: ADG5208 and ADG5209 Redesign resulting in Data Sheet Specification Changes

Publication Date: 09-Dec-2014

Effectivity Date: 10-Dec-2014 *(the earliest date that a customer could expect to receive changed material)*

Revision Description:

Date code change over added

Description Of Change

All layer redesign of the ADG5208 and ADG5209 die which results in improved ESD ratings and affects product specifications for charge injection, pin capacitance, timing, bandwidth, cross talk and isolation. Please see attachment for change details.

Reason For Change

Improvement for ESD rating, charge injection and timing specifications.

Impact of the change (positive or negative) on fit, form, function & reliability

This transfer will not affect the form, fit, function, quality or reliability of the ADG5208 and the ADG5209

Product Identification *(this section will describe how to identify the changed material)*

The date code changeover of the TSSOP models will be 1435.

LFCSP models will continue to conform to the specifications in Revision A of the data sheet.

Summary of Supporting Information

Qualification has been performed per ADI0012, Procedure for Qualification of New or Revised Processes. See attached Qualification Report Summary.

Supporting Documents

Attachment 1: Type: Datasheet Specification Comparison

ADI_PCN_14_0067_Rev_A_ADG5208_09 RevA to RevB Data Sheet Changes.pdf

Attachment 2: Type: Qualification Results Summary

ADI_PCN_14_0067_Rev_A_Qual Summary ADG5208 ADG5209.pdf

For questions on this PCN, please send an email to the regional contacts below or contact your local ADI sales representatives.

Americas: PCN_Americas@analog.com

Europe: PCN_Europe@analog.com

Japan: PCN_Japan@analog.com

Rest of Asia: PCN_ROA@analog.com

Appendix A - Affected ADI Models

Existing Parts - Product Family / Model Number (4)

ADG5208 / ADG5208BRUZ	ADG5208 / ADG5208BRUZ-RL7	ADG5209 / ADG5209BRUZ	ADG5209 / ADG5209BRUZ-RL7	
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Appendix B - Revision History

Rev	Publish Date	Effectivity Date	Rev Description
Rev. -	04-Sep-2014	02-Dec-2014	Initial Release
Rev. A	09-Dec-2014	10-Dec-2014	Date code change over added

Analog Devices, Inc.

DocId:3148 Parent DocId:None Layout Rev:7

PCN 14_0067

ADG5208/ADG5209 Data Sheet Changes

Rev. A to Rev. B

This document highlights the performance differences between the Rev.A and Rev.B data sheet for the ADG5208 and ADG5209 Analog Multiplexers.

For full product information and changes to Typical Performance Characteristics plots please refer to the ADG5208/09 Rev.B data sheet.

1. HBM ESD

HBM ESD	Rev A	Rev B
I/O Port to Supplies	4kV	8kV
I/O Port to I/O Port	1kV	2kV
All other pins	4kV	8kV

2. Datasheet specification changes from Rev. A to Rev. B

Tables 1 to 4 outline a datasheet specification comparison of Rev. A to Rev. B material. The changed specifications are highlighted in red font.

SPECIFICATION CHANGES FROM Rev. A to Rev. B

Table 1. $V_{DD} = +15\text{ V} \pm 10\%$, $V_{SS} = -15\text{ V} \pm 10\%$, $GND = 0\text{ V}$, unless otherwise noted.

Parameter	Rev. A			Rev. B			Unit	Test Conditions/ Comments
	25°C	-40°C to +85°C	-40°C to +125°C	25°C	-40°C to +85°C	-40°C to +125°C		
ANALOG SWITCH								
Analog Signal Range	V_{DD} to V_{SS}			V_{DD} to V_{SS}			V	$V_S = \pm 10\text{ V}$, $I_S = -1\text{ mA}$ $V_{DD} = +13.5\text{ V}$, $V_{SS} = -13.5\text{ V}$ $V_S = \pm 10\text{ V}$, $I_S = -1\text{ mA}$ $V_S = \pm 10\text{ V}$, $I_S = -1\text{ mA}$
On Resistance, R_{ON}	160			160			Ω typ	
On-Resistance Match Between Channels, ΔR_{ON}	200	250	280	200	250	280	Ω max	
On-Resistance Flatness, $R_{FLAT(ON)}$	3.5			3.5			Ω typ	
	8	9	10	8	9	10	Ω max	
	40			40			Ω typ	$V_S = \pm 10\text{ V}$, $I_S = -1\text{ mA}$
	50	65	70	50	65	70	Ω max	
LEAKAGE CURRENTS								
Source Off Leakage, I_S (Off)	± 0.005			± 0.005			nA typ	$V_{DD} = +16.5\text{ V}$, $V_{SS} = -16.5\text{ V}$ $V_S = \pm 10\text{ V}$, $V_D = \pm 10\text{ V}$
	± 0.1	± 0.2	± 0.4	± 0.1	± 0.2	± 0.4	nA max	
Drain Off Leakage, I_D (Off)	± 0.005			± 0.005			nA typ	$V_S = \pm 10\text{ V}$, $V_D = \pm 10\text{ V}$
	± 0.1	± 0.4	± 1.4	± 0.1	± 0.4	± 1.4	nA max	
Channel On Leakage, I_D (On), I_S (On)	± 0.01			± 0.01			nA typ	$\pm V_S = V_D = \pm 10\text{ V}$
	± 0.2	± 0.5	± 1.4	± 0.2	± 0.5	± 1.4	nA max	
DIGITAL INPUTS								
Input High Voltage, V_{INH}			2			2	V min	$V_{IN} = V_{GND}$ or V_{DD}
Input Low Voltage, V_{INL}			0.8			0.8	V max	
Input Current, I_{INL} or I_{INH}	0.002			0.002			μA typ	
			± 0.1			± 0.1	μA max	
Digital Input Capacitance, C_{IN}	3			3			pF typ	
Dynamic Characteristics¹								
Transition Time, $t_{TRANSITION}$	170			150			ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$ $V_S = 10\text{ V}$
	205	245	275	180	210	245	ns max	
t_{ON} (EN)	145			125			ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$ $V_S = 10\text{ V}$
	185	220	245	150	185	215	ns max	
t_{OFF} (EN)	120			160			ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$ $V_S = 10\text{ V}$
	145	165	180	185	210	230	ns max	
Break-Before-Make Time Delay, t_D	65			55			ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$ $V_{S1} = V_{S2} = 10\text{ V}$ $V_S = 0\text{ V}$, $R_S = 0\ \Omega$, $C_L = 1\text{ nF}$
Charge Injection, Q_{NJ}	0.4			0.2			ns min	
Off Isolation	-90			-86			pC typ	dB typ
Channel-to-Channel Crosstalk -3 dB Bandwidth	-90			-80			dB typ	
ADG5208	54			110			MHz typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$
ADG5209	133			240			MHz typ	
Insertion Loss	-6.4			-6.4			dB typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$ $V_S = 0\text{ V}$, $f = 1\text{ MHz}$
C_S (Off)	5.5			2.9			pF typ	
C_D (Off)							pF typ	$V_S = 0\text{ V}$, $f = 1\text{ MHz}$ $V_S = 0\text{ V}$, $f = 1\text{ MHz}$
ADG5208	52			34			pF typ	
ADG5209	26			17			pF typ	
C_D (On), C_S (On)							pF typ	$V_S = 0\text{ V}$, $f = 1\text{ MHz}$ $V_S = 0\text{ V}$, $f = 1\text{ MHz}$
ADG5208	58			37			pF typ	
ADG5209	31			21			pF typ	
POWER REQUIREMENTS								
I_{DD}	45			45			μA typ	$V_{DD} = +16.5\text{ V}$, $V_{SS} = -16.5\text{ V}$ Digital inputs = 0 V or V_{DD}
	55		70	55		70	μA max	
I_{SS}	0.001			0.001			μA typ	Digital inputs = 0 V or V_{DD}
			1			1	μA max	
V_{DD}/V_{SS}			$\pm 9/\pm 22$			$\pm 9/\pm 22$	V min/V max	$GND = 0\text{ V}$

¹ Guaranteed by design, not subject to production test.

Table 2. $V_{DD} = +20V \pm 10\%$, $V_{SS} = -20V \pm 10\%$, $GND = 0V$, unless otherwise noted.

Parameter	Rev. A			Rev. B			Unit	Test Conditions/ Comments
	25°C	-40°C to +85°C	-40°C to +125°C	25°C	-40°C to +85°C	-40°C to +125°C		
ANALOG SWITCH								
Analog Signal Range			V_{DD} to V_{SS}			V_{DD} to V_{SS}	V	
On Resistance, R_{ON}	140			140			Ω typ	$V_S = \pm 15V$, $I_S = -1mA$
On-Resistance Match Between Channels, ΔR_{ON}	160	200	230	160	200	230	Ω max	$V_{DD} = +18V$, $V_{SS} = -18V$
On-Resistance Flatness, $R_{RELAT(ON)}$	3.5			3.5			Ω typ	$V_S = \pm 15V$, $I_S = -1mA$
	8	9	10	8	9	10	Ω max	
	34			34			Ω typ	$V_S = \pm 15V$, $I_S = -1mA$
	45	55	60	45	55	60	Ω max	
LEAKAGE CURRENTS								
Source Off Leakage, I_S (Off)	± 0.005			± 0.005			nA typ	$V_{DD} = +22V$, $V_{SS} = -22V$
	± 0.1	± 0.2	± 0.4	± 0.1	± 0.2	± 0.4	nA max	$V_S = \pm 15V$, $V_D = \pm 15V$
Drain Off Leakage, I_D (Off)	± 0.005			± 0.005			nA typ	$V_S = \pm 15V$, $V_D = \pm 15V$
	± 0.1	± 0.4	± 1.4	± 0.1	± 0.4	± 1.4	nA max	
Channel On Leakage, I_D (On), I_S (On)	± 0.01			± 0.01			nA typ	$\pm V_S = V_D = \pm 15V$
	± 0.2	± 0.5	± 1.4	± 0.2	± 0.5	± 1.4	nA max	
DIGITAL INPUTS								
Input High Voltage, V_{INH}			2			2	V min	
Input Low Voltage, V_{INL}			0.8			0.8	V max	
Input Current, I_{INL} or I_{INH}	0.002			0.002			μA typ	$V_{IN} = V_{GND}$ or V_{DD}
			± 0.1			± 0.1	μA max	
Digital Input Capacitance, C_{IN}	3			3			pF typ	
DYNAMIC CHARACTERISTICS¹								
Transition Time, $t_{TRANSITION}$	160			140			ns typ	$R_L = 300\Omega$, $C_L = 35pF$
	195	225	255	170	195	220	ns max	$V_S = 10V$
t_{ON} (EN)	145			120			ns typ	$R_L = 300\Omega$, $C_L = 35pF$
	170	200	225	140	170	195	ns max	$V_S = 10V$
t_{OFF} (EN)	120			160			ns typ	$R_L = 300\Omega$, $C_L = 35pF$
	140	155	170	185	205	220	ns max	$V_S = 10V$
Break-Before-Make Time Delay, t_D	55			45			ns typ	$R_L = 300\Omega$, $C_L = 35pF$
			30			20	ns min	$V_{S1} = V_{S2} = 10V$
Charge Injection, Q_{INJ}	0.3			0.4			pC typ	$V_S = 0V$, $R_S = 0\Omega$, $C_L = 1nF$
Off Isolation	-90			-86			dB typ	$R_L = 50\Omega$, $C_L = 5pF$, $f = 1MHz$
Channel-to-Channel Crosstalk	-90			-80			dB typ	$R_L = 50\Omega$, $C_L = 5pF$, $f = 1MHz$
-3 dB Bandwidth							MHz typ	$R_L = 50\Omega$, $C_L = 5pF$
ADG5208	60			121			MHz typ	
ADG5209	130			255			MHz typ	
Insertion Loss	-5.6			-5.6			dB typ	$R_L = 50\Omega$, $C_L = 5pF$, $f = 1MHz$; see
C_S (Off)	5.5			2.8			pF typ	$V_S = 0V$, $f = 1MHz$
C_D (Off)							pF typ	
ADG5208	51			33			pF typ	$V_S = 0V$, $f = 1MHz$
ADG5209	26			17			pF typ	$V_S = 0V$, $f = 1MHz$
C_D (On), C_S (On)							pF typ	
ADG5208	57			36			pF typ	$V_S = 0V$, $f = 1MHz$
ADG5209	31			21			pF typ	$V_S = 0V$, $f = 1MHz$
POWER REQUIREMENTS								
I_{DD}	50			50			μA typ	$V_{DD} = +22V$, $V_{SS} = -22V$
	70		110	70		110	μA max	Digital inputs = 0V or V_{DD}
I_{SS}	0.001			0.001			μA typ	Digital inputs = 0V or V_{DD}
			1			1	μA max	
V_{DD}/V_{SS}			$\pm 9/\pm 22$			$\pm 9/\pm 22$	V min/V max	$GND = 0V$

¹ Guaranteed by design, not subject to production test.

Table 3. $V_{DD} = +12V \pm 10\%$, $V_{SS} = 0V$ $GND = 0V$, unless otherwise noted.

Parameter	Rev. A			Rev. B			Unit	Test Conditions/ Comments
	25°C	-40°C to +85°C	-40°C to +125°C	25°C	-40°C to +85°C	-40°C to +125°C		
ANALOG SWITCH								
Analog Signal Range	0 V to V_{DD}			0 V to V_{DD}			V	
On Resistance, R_{ON}	350			350			Ω typ	$V_S = 0V$ to $10V$, $I_S = -1$ mA $V_{DD} = +10.8V$, $V_{SS} = 0$ V
On-Resistance Match Between Channels, ΔR_{ON}	500	610	700	500	610	700	Ω max	
On-Resistance Flatness, $R_{RELAT(ON)}$	5			5			Ω typ	$V_S = 0V$ to $10V$, $I_S = -1$ mA
	20	22	24	20	22	24	Ω max	
	160			160			Ω typ	$V_S = 0V$ to $10V$, $I_S = -1$ mA
	280	335	370	280	335	370	Ω max	
LEAKAGE CURRENTS								
Source Off Leakage, I_S (Off)	± 0.00 5			± 0.00 5			nA typ	$V_{DD} = 13.2V$, $V_{SS} = 0V$ $V_S = 1V/10V$, $V_D = +10$ V/1V
	± 0.1	± 0.2	± 0.4	± 0.1	± 0.2	± 0.4	nA max	
Drain Off Leakage, I_D (Off)	± 0.00 5			± 0.00 5			nA typ	$V_S = 1V/10V$, $V_D = +10$ V/1V
	± 0.1	± 0.4	± 1.4	± 0.1	± 0.4	± 1.4	nA max	
Channel On Leakage, I_D (On), I_S (On)	± 0.01			± 0.01			nA typ	$\pm V_S = V_D = 1$ V/10V
	± 0.2	± 0.5	± 1.4	± 0.2	± 0.5	± 1.4	nA max	
DIGITAL INPUTS								
Input High Voltage, V_{INH}			2			2	V min	$V_{IN} = V_{GND}$ or V_{DD}
Input Low Voltage, V_{INL}			0.8			0.8	V max	
Input Current, I_{INL} or I_{INH}	0.002			0.002			μA typ	
			± 0.1			± 0.1	μA max	
Digital Input Capacitance, C_{IN}	3			3			pF typ	
DYNAMIC CHARACTERISTICS¹								
Transition Time, $t_{TRANSITION}$	210 270			200 250			ns typ ns max	$R_L = 300\ \Omega$, $C_L = 35$ pF $V_S = 8V$
t_{ON} (EN)	215 275	330	380	180 225	295	335	ns typ ns max	
t_{OFF} (EN)	115 140	345	400	165 200	280	320	ns typ ns max	$R_L = 300\ \Omega$, $C_L = 35$ pF $V_S = 8V$
Break-Before-Make Time Delay, t_D	135	160	175	95	225	245	ns typ ns min	
Charge Injection, Q_{INJ}	0.3			0.2			pC typ	$R_L = 300\ \Omega$, $C_L = 35$ pF $V_{S1} = V_{S2} = 8V$
Off Isolation	-90			-86			dB typ	$V_S = 6V$, $R_S = 0\ \Omega$, $C_L = 1$ nF
Channel-to-Channel Crosstalk -3 dB Bandwidth	-90			-80			dB typ	$R_L = 50\ \Omega$, $C_L = 5$ pF, $f = 1$ MHz
ADG5208	60			95			MHz typ	$R_L = 50\ \Omega$, $C_L = 5$ pF, $f = 1$ MHz
ADG5209	120			180			MHz typ	
Insertion Loss	-8.8			-8.9			dB typ	$R_L = 50\ \Omega$, $C_L = 5$ pF, $f = 1$ MHz; see
C_S (Off)	6			3.3			pF typ	$V_S = 0V$, $f = 1$ MHz
C_D (Off)							pF typ	$V_S = 0V$, $f = 1$ MHz
ADG5208	56			38			pF typ	
ADG5209	28			19			pF typ	$V_S = 0V$, $f = 1$ MHz
C_D (On), C_S (On)							pF typ	$V_S = 0V$, $f = 1$ MHz
ADG5208	63			41			pF typ	
ADG5209	35			24			pF typ	$V_S = 0V$, $f = 1$ MHz
POWER REQUIREMENTS								
I_{DD}	40			40			μA typ	$V_{DD} = 13.2$ Digital inputs = 0 V or V_{DD}
	50		65	50		65	μA max	
V_{DD}		9/40			9/40		V min/V max	$GND = 0V$, $V_{SS} = 0V$

¹ Guaranteed by design, not subject to production test.

Table 4. $V_{DD} = +36V \pm 10\%$, $V_{SS} = 0V$ $GND = 0V$, unless otherwise noted.

Parameter	Rev.A			Rev. B			Unit	Test Conditions/ Comments
	25°C	-40°C to +85°C	-40°C to +125°C	25°C	-40°C to +85°C	-40°C to +125°C		
ANALOG SWITCH								
Analog Signal Range	0 V to V_{DD}			0 V to V_{DD}			V	
On Resistance, R_{ON}	150			150			Ω typ	$V_S = \pm 10V$, $I_S = -1mA$ $V_{DD} = +13.5V$, $V_{SS} = -13.5V$ $V_S = \pm 10V$, $I_S = -1mA$ $V_S = \pm 10V$, $I_S = -1mA$
On-Resistance Match Between Channels, ΔR_{ON}	170	215	245	170	215	245	Ω max	
On-Resistance Flatness, $R_{FLAT(ON)}$	3.5			3.5			Ω typ	
	8	9	10	8	9	10	Ω max	
	35			35			Ω typ	
	55	65	70	55	65	70	Ω max	
LEAKAGE CURRENTS								
Source Off Leakage, I_S (Off)	± 0.00 5			± 0.00 5			nA typ	$V_{DD} = +16.5V$, $V_{SS} = -16.5V$ $V_S = \pm 10V$, $V_D = \pm 10V$
	± 0.1	± 0.2	± 0.4	± 0.1	± 0.2	± 0.4	nA max	
Drain Off Leakage, I_D (Off)	± 0.00 5			± 0.00 5			nA typ	$V_S = \pm 10V$, $V_D = \pm 10V$
	± 0.1	± 0.4	± 1.4	± 0.1	± 0.4	± 1.4	nA max	
Channel On Leakage, I_D (On), I_S (On)	± 0.01			± 0.01			nA typ	$V_S = V_D = \pm 10V$;
	± 0.2	± 0.5	± 1.4	± 0.2	± 0.5	± 1.4	nA max	
DIGITAL INPUTS								
Input High Voltage, V_{INH}			2			2	V min	$V_{IN} = V_{GND}$ or V_{DD}
Input Low Voltage, V_{INL}			0.8			0.8	V max	
Input Current, I_{INL} or I_{INH}	0.002			0.002			μA typ	
		± 0.1			± 0.1		μA max	
Digital Input Capacitance, C_{IN}	3			3			pF typ	
DYNAMIC CHARACTERISTICS¹								
Transition Time, $t_{TRANSITION}$	185 230			170 205			ns typ ns max	$R_L = 300\Omega$, $C_L = 35pF$ $V_S = 10V$
t_{ON} (EN)	170 210	245	259	150 180	225	235	ns typ ns max	
t_{OFF} (EN)	125 180	230	255	180 225	195	215	ns typ ns max	$R_L = 300\Omega$, $C_L = 35pF$ $V_S = 10V$
Break-Before-Make Time Delay, t_D	70	180	180	55	225	230	ns typ ns min	
Charge Injection, Q_{INJ}	0.4			0.3			pC typ	$R_L = 300\Omega$, $C_L = 35pF$ $V_{S1} = V_{S2} = 10V$ $V_S = 0V$, $R_S = 0\Omega$, $C_L = 1nF$
Off Isolation	-90			-86			dB typ	
Channel-to-Channel Crosstalk	-90			-80			dB typ	$R_L = 50\Omega$, $C_L = 5pF$, $f = 1MHz$ $R_L = 50\Omega$, $C_L = 5pF$, $f = 1MHz$ $R_L = 50\Omega$, $C_L = 5pF$
-3 dB Bandwidth								
ADG5208	65			105			MHz typ	$R_L = 50\Omega$, $C_L = 5pF$, $f = 1MHz$; see $V_S = 0V$, $f = 1MHz$
ADG5209	130			195			MHz typ	
Insertion Loss	-6			-6.2			dB typ	$R_L = 50\Omega$, $C_L = 5pF$, $f = 1MHz$ $V_S = 0V$, $f = 1MHz$
C_S (Off) C_D (Off)	5.5			2.7			pF typ	
ADG5208	51			32			pF typ	$V_S = 0V$, $f = 1MHz$ $V_S = 0V$, $f = 1MHz$
ADG5209	25			16			pF typ	
C_D (On), C_S (On)								$V_S = 0V$, $f = 1MHz$ $V_S = 0V$, $f = 1MHz$
ADG5208	57			35			pF typ	
ADG5209	32			20			pF typ	
POWER REQUIREMENTS								
I_{DD}	80			80			μA typ	$V_{DD} = +16.5V$, $V_{SS} = -16.5V$ Digital inputs = 0V or V_{DD}
	100		130	100		130	μA max	
V_{DD}		9/40			9/40		V min/V max	$GND = 0V$, $V_{SS} = 0V$

¹ Guaranteed by design, not subject to production test.